## TOSHIBA VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

## 1 S V 2 1 5

CATV TUNING.

High Capacitance Ratio :  $C_{2V}/C_{25V}=10.5$  (Typ.)

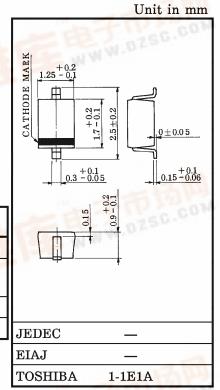
Low Series Resistance :  $r_S = 0.6\Omega$  (Typ.)

Excellent C-V Characteristics, and Small Tracking Error.

Useful for Small Size Tuner.

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	$v_{R}$	30	V
Peak Reverse Voltage	$V_{RM}$	$\frac{35}{(R_L=10k\Omega)}$	V
Junction Temperature	$\mathbf{T}_{\mathbf{j}}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	$^{\circ}\mathrm{C}$



Weight: 0.004g

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

BOL TEST CONDITION $I_R = 1\mu A$	MIN.	TYP.	MAX.	UNIT
In-1A				
$\mathbf{R} - \mathbf{I} \mu \mathbf{R}$	30	_	_	V
$V_R = 28V$	_		10	nA
$V_R=2V$ , $f=1MHz$	26	_	32	pF
$V_R$ =25V, f=1MHz	2.5	_	3.2	pF
C <sub>25V</sub> —	9.5	10.5	-17	
$V_R = 5V$ , $f = 470MHz$	T	0.6	0.8	Ω
	V <sub>R</sub> =2V, f=1MHz V <sub>R</sub> =25V, f=1MHz 25V —	$V_R = 2V, f = 1MHz$ 26 $V_R = 25V, f = 1MHz$ 2.5 $V_R = 25V$ — 9.5	$V_{R}=2V, f=1MHz$ 26 — $V_{R}=25V, f=1MHz$ 2.5 — 9.5 10.5	$V_R = 2V$ , $f = 1MHz$

Note 1: Available in matched group for capacitance to 2.5%.

$$\frac{C \text{ (Max.)} - C \text{ (Min.)}}{C \text{ (Min.)}} \leq 0.025$$

$$(V_R = 2 \sim 25V)$$

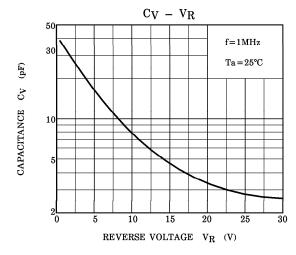
Marking

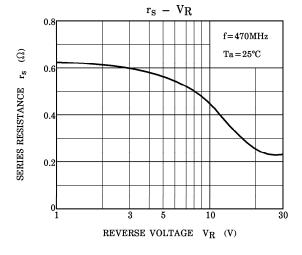
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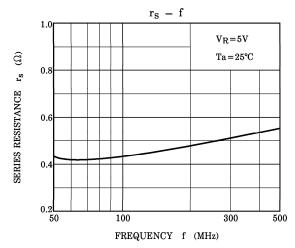
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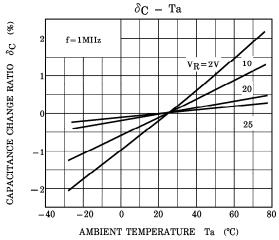
The information contained herein is subject to change without notice.

TOSHIBA 1SV215









NOTE : 
$$\delta_{\text{C}}$$
 (%) =  $\frac{\text{C (Ta)} - \text{C (25)}}{\text{C (25)}} \times 100$